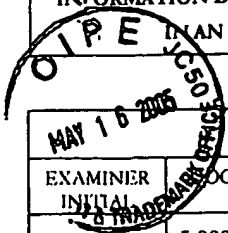


Form 1449*	Docket Number: G&C 30794.79-US-U1	Application Number: 09/922,122
INFORMATION DISCLOSURE STATEMENT		
Applicant: Hugues Marchand et al.		
Filing Date: August 3, 2001		Group Art Unit: 1765



U.S. PATENT DOCUMENTS						
EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE
M>	5,880,485	03/09/99	Marx et al.			
	6,153,010	11/28/00	Kiyoku et al.			
	6,180,270	01/30/01	Cole et al.			
	6,291,319	09/18/01	Yu et al.			
	6,328,796	12/11/01	Kub et al.			
	6,358,770	03/19/02	Itoh et al.			
	6,391,748	05/21/02	Temkin et al.			
	6,420,197	07/16/02	Ishida et al.			
	6,440,823	08/27/02	Vaudo et al.			
	6,459,712	10/01/02	Tanaka et al.			
	6,524,932	02/25/03	Zhang et al.			
	6,548,333	04/15/03	Smith			
	6,610,144	08/26/03	Mishra et al.			
	6,707,074	03/16/04	Yoshii et al.			
M>	6,765,240	07/20/04	Tischler et al.			

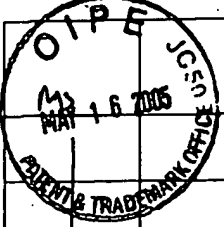
FOREIGN PATENTS							
	DOCUMENT NO.	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
						YES	NO

NON-PATENT DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)		
M>		Bykhovski, A.D. et al., "Elastic strain relaxation in GaN-AlN-GaN semiconductor - insulator - semiconductor structures," J. Appl. Phys. 78(6):3691-3696, September 15, 1995
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M>		Guha, S. et al., "Ultraviolet and violet GaN light emitting diodes on silicon," Appl. Phys. Lett. 72(4):415-417, January 26, 1998

EXAMINER: <i>Matt S</i>	DATE CONSIDERED: <i>7/18/2005</i>
EXAMINER: Initial if reference considered whether or not citation is in conformance with MPEP 609; draw line through citation if not in conformance and not considered. Include copy of this form for next communication to the Applicant.	

Form 1449* <b>INFORMATION DISCLOSURE STATEMENT</b> <b>IN AN APPLICATION</b>	Docket Number: G&C 30794.79-US-U1	Application Number: 09/922,122
	Applicant: Hugues Marchand et al.	
	Filing Date: August 3, 2001	Group Art Unit: 1765

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M7	Zhao, Z.M. et al., "Metal-semiconductor-metal GaN ultraviolet photodetectors on Si(111)," Applied Physics Letters, 77(3):444-446, July 17, 2000

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